

# 2N5609

Silicon PNP Transistors

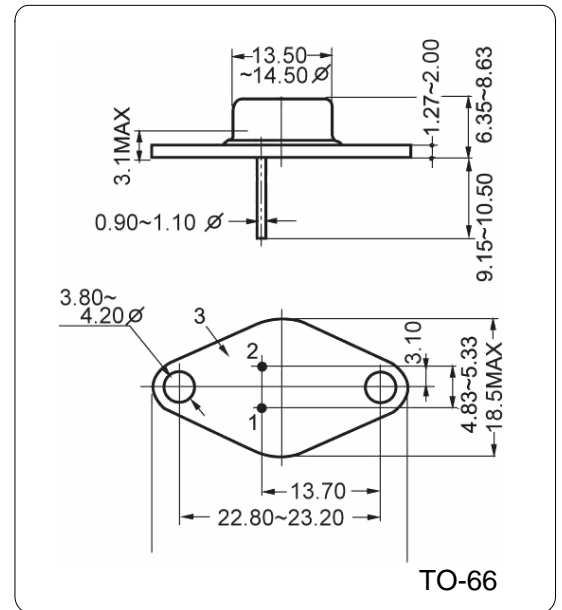


## ◆ Features

- With TO-66 package
- Designed for use as high-frequency drivers in audio amplifier

## ◆ Absolute Maximum Ratings Tc=25°C

SYMBOL	PARAMETER	RATING	UNIT
V <sub>CBO</sub>	Collector to base voltage	80	V
V <sub>CEO</sub>	Collector to emitter voltage	80	V
V <sub>EBO</sub>	Emitter to base voltage	5.0	V
I <sub>CP</sub>	Peak collector current		A
I <sub>C</sub>	Collector current	5.0	A
P <sub>C</sub>	Collector power dissipation	25	W
T <sub>j</sub>	Junction temperature	150	°C
T <sub>stg</sub>	Storage temperature	-55~150	°C



## ◆ Electrical Characteristics Tc=25°C

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I <sub>CBO</sub>	Collector-base cut-off current	V <sub>CB</sub> =80V; I <sub>E</sub> =0		10	μ A
I <sub>EBO</sub>	Emitter-base cut-off current	V <sub>EB</sub> =5V, I <sub>C</sub> =0		10	μ A
I <sub>CEO</sub>	Collector-emitter cut-off current				
V <sub>CBO</sub>	Collector-base breakdown voltage				
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0	80		V
V <sub>EBO</sub>	Emitter-base breakdown voltage				
V <sub>CEsat-1</sub>	Collector-emitter saturation voltages	I <sub>C</sub> =1A; I <sub>B</sub> =0.1A		0.5	V
V <sub>CEsat-2</sub>	Collector-emitter saturation voltages				
V <sub>CEsat-3</sub>	Collector-emitter saturation voltages				
V <sub>CEsat-4</sub>	Collector-emitter saturation voltages				
h <sub>FE-1</sub>	Forward current transfer ratio	I <sub>C</sub> =2.5A, V <sub>CE</sub> =5V	70	200	
h <sub>FE-2</sub>	Forward current transfer ratio				
h <sub>FE-3</sub>	Forward current transfer ratio				
h <sub>FE-4</sub>	Forward current transfer ratio				
V <sub>BE(sat)1</sub>	Base-emitter saturation voltages	I <sub>C</sub> =1A, V <sub>CE</sub> =2V		1.0	V
V <sub>BE(sat)2</sub>	Base-emitter saturation voltages				
V <sub>BE(sat)3</sub>	Base-emitter saturation voltages				
f <sub>T</sub>	Transition frequency at f = 1MHz				
t <sub>f</sub>	Fall time				
t <sub>s</sub>	Turn-off storage time				